

MOSFETs Silicon N-channel MOS (U-MOSX-H)

TPH1400CQH

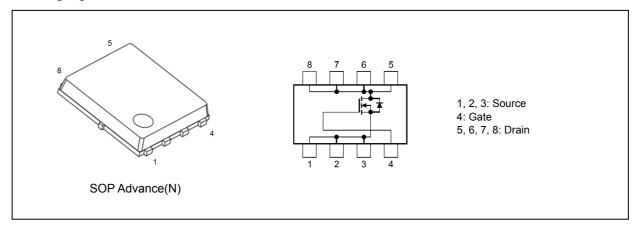
1. Applications

- · High-Efficiency DC-DC Converters
- · Switching Voltage Regulators
- · Motor Drivers

2. Features

- (1) High-speed switching
- (2) Small gate charge: $Q_{SW} = 8.5 \text{ nC (typ.)}$
- (3) Small output charge: $Q_{oss} = 56 \text{ nC (typ.)}$
- (4) Low drain-source on-resistance: $R_{DS(ON)} = 11.4 \text{ m}\Omega$ (typ.) ($V_{GS} = 10 \text{ V}$)
- (5) Low leakage current: $I_{DSS} = 10 \mu A (max) (V_{DS} = 150 V)$
- (6) Enhancement mode: V_{th} = 3.3 to 4.3 V (V_{DS} = 10 V, I_D = 0.6 mA)

3. Packaging and Internal Circuit





4. Absolute Maximum Ratings (Note) (T_a = 25 °C unless otherwise specified)

| Characteris | Symbol | Rating | Unit | | |
|--------------------------------|--------------------------|--------------------|------------------|------------|----|
| Drain-source voltage | | | V_{DSS} | 150 | V |
| Gate-source voltage | , | | V_{GSS} | ±20 | |
| Drain current (DC) | (T _c = 25 °C) | (Note 1) | I _D | 32 | Α |
| Drain current (DC) | (Silicon limit) | (Note 1), (Note 2) | I_D | 77 | |
| Drain current (pulsed) | (t = 100 μs) | (Note 1) | I _{DP} | 190 | |
| Power dissipation | (T _c = 25 °C) | | P_{D} | 170 | W |
| Power dissipation | , | (Note 3) | P_{D} | 3 | |
| Power dissipation | , | (Note 4) | P_{D} | 0.96 | |
| Single-pulse avalanche energy | | (Note 5) | E _{AS} | 97 | mJ |
| Single-pulse avalanche current | | (Note 5) | I _{AS} | 32 | Α |
| Channel temperature | | | T _{ch} | 175 | °C |
| Storage temperature | | | T _{stg} | -55 to 175 | |

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

5. Thermal Characteristics

| Characteristics | | | Max | Unit |
|-------------------------------------------------------------|----------|-----------------------|------|------|
| Channel-to-case thermal resistance (T _c = 25 °C) | | R _{th(ch-c)} | 0.88 | °C/W |
| Channel-to-ambient thermal resistance | (Note 3) | R _{th(ch-a)} | 50 | |
| Channel-to-ambient thermal resistance | (Note 4) | R _{th(ch-a)} | 156 | |

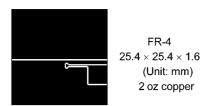
Note 1: Ensure that the channel temperature does not exceed 175 °C.

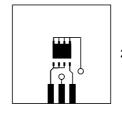
Note 2: Limited by silicon chip capability.

Note 3: Device mounted on a glass-epoxy board (a), Figure 5.1

Note 4: Device mounted on a glass-epoxy board (b), Figure 5.2

Note 5: V_{DD} = 120 V, T_{ch} = 25 °C (initial), L = 73 μ H, I_{AS} = 32 A





FR-4 $25.4 \times 25.4 \times 1.6$ (Unit: mm) 2 oz copper

Fig. 5.1 Device Mounted on a Glass-Epoxy Board (a)

Fig. 5.2 Device Mounted on a Glass-Epoxy Board (b)

Note: This transistor is sensitive to electrostatic discharge and should be handled with care.



6. Electrical Characteristics

6.1. Static Characteristics (T_a = 25 °C unless otherwise specified)

| Characteristics | Symbol | Test Condition | Min | Тур. | Max | Unit |
|-----------------------------------------|----------------------|---------------------------------------------------|-----|------|------|------|
| Gate leakage current | I _{GSS} | $V_{GS} = \pm 20 \text{ V}, V_{DS} = 0 \text{ V}$ | _ | _ | ±0.1 | μА |
| Drain cut-off current | I _{DSS} | V _{DS} = 150 V, V _{GS} = 0 V | _ | _ | 10 | |
| Drain-source breakdown voltage | V _{(BR)DSS} | I _D = 10 mA, V _{GS} = 0 V | 150 | | | ٧ |
| Drain-source breakdown voltage (Note 6) | V _{(BR)DSX} | $I_D = 10 \text{ mA}, V_{GS} = -20 \text{ V}$ | 130 | | | |
| Gate threshold voltage | V_{th} | $V_{DS} = 10 \text{ V}, I_D = 0.6 \text{ mA}$ | 3.3 | _ | 4.3 | |
| Drain-source on-resistance | R _{DS(ON)} | V _{GS} = 8 V, I _D = 16 A | _ | 12.4 | 17.3 | mΩ |
| | | V _{GS} = 10 V, I _D = 16 A | _ | 11.4 | 14.1 | |

Note 6: If a reverse bias is applied between gate and source, this device enters $V_{(BR)DSX}$ mode. Note that the drain-source breakdown voltage is lowered in this mode.

6.2. Dynamic Characteristics (T_a = 25 °C unless otherwise specified)

| Characteristics | Symbol | Test Condition | Min | Тур. | Max | Unit |
|--------------------------------|------------------|----------------------------------------------------------|-----|------|------|------|
| Input capacitance | C _{iss} | V _{DS} = 75 V, V _{GS} = 0 V, f = 1 MHz | _ | 2400 | 3800 | pF |
| Reverse transfer capacitance | C _{rss} | | _ | 16 | 50 | |
| Output capacitance | C _{oss} | | _ | 450 | _ | |
| Gate resistance | r _g | _ | _ | 1.2 | 1.8 | Ω |
| Switching time (rise time) | t _r | See Fig. 6.2.1 | _ | 11.4 | _ | ns |
| Switching time (turn-on time) | t _{on} | | _ | 30 | _ | |
| Switching time (fall time) | t _f | | _ | 11.6 | _ | |
| Switching time (turn-off time) | t _{off} | | _ | 32 | _ | |

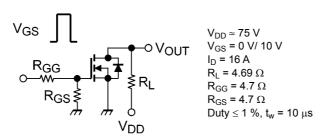


Fig. 6.2.1 Switching Time Test Circuit

6.3. Gate Charge Characteristics (T_a = 25 °C unless otherwise specified)

| Characteristics | Symbol | Test Condition | Min | Тур. | Max | Unit |
|-------------------------------------|------------------|----------------------------------------------------------------------------|-----|------|-----|------|
| Total gate charge (gate-source plus | Q_g | $V_{DD} \approx 75 \text{ V}, V_{GS} = 10 \text{ V}, I_{D} = 16 \text{ A}$ | _ | 31 | | nC |
| gate-drain) | | $V_{DD} \approx 75 \text{ V}, V_{GS} = 8 \text{ V}, I_{D} = 16 \text{ A}$ | _ | 25 | | |
| Gate-source charge 1 | Q _{gs1} | $V_{DD} \approx 75 \text{ V}, V_{GS} = 10 \text{ V}, I_{D} = 16 \text{ A}$ | _ | 13 | | |
| Gate-drain charge | Q_{gd} | | _ | 5.1 | _ | |
| Gate switch charge | Q_{SW} | | _ | 8.5 | _ | |
| Output charge | Q_{oss} | V _{DS} = 75 V, V _{GS} = 0 V, f = 1 MHz | _ | 56 | _ | |



6.4. Source-Drain Characteristics ($T_a = 25$ °C unless otherwise specified)

| Characteristics | Symbol | Test Condition | Min | Тур. | Max | Unit |
|-----------------------------------------|------------------|-----------------------------------------------|-----|------|------|------|
| Reverse drain current (pulsed) (Note 7) | I _{DRP} | (t = 100 μs) | _ | _ | 190 | Α |
| Diode forward voltage | V _{DSF} | I _{DR} = 16 A, V _{GS} = 0 V | _ | _ | -1.2 | V |
| Reverse recovery time | t _{rr} | $I_{DR} = 8 A, V_{GS} = 0 V,$ | _ | 66 | _ | ns |
| Reverse recovery charge | Q _{rr} | -dI _{DR} /dt = 100 A/μs | _ | 107 | _ | nC |

Note 7: Ensure that the channel temperature does not exceed 175 °C.

7. Marking

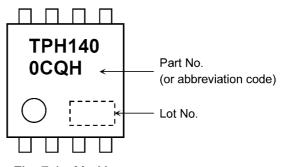


Fig. 7.1 Marking



8. Characteristics Curves (Note)

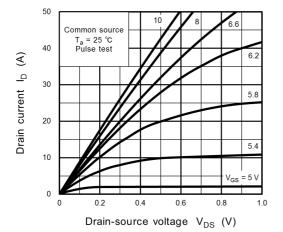


Fig. 8.1 I_D - V_{DS}

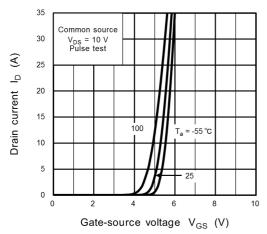


Fig. 8.3 I_D - V_{GS}

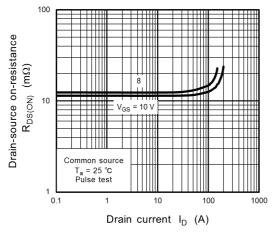


Fig. 8.5 R_{DS(ON)} - I_D

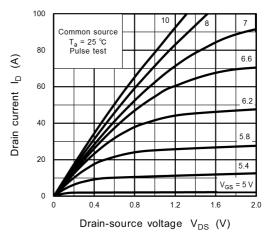


Fig. 8.2 I_D - V_{DS}

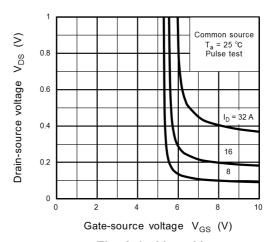


Fig. 8.4 VDS - VGS

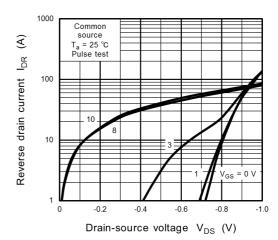


Fig. 8.6 IDR - VDS



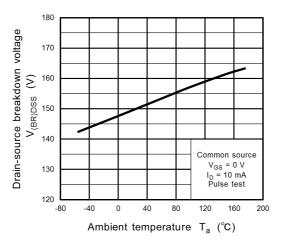


Fig. 8.7 V_{(BR)DSS} - T_a

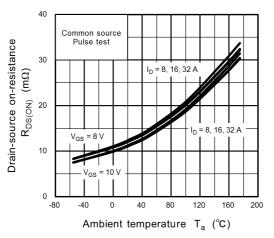


Fig. 8.9 R_{DS(ON)} - T_a

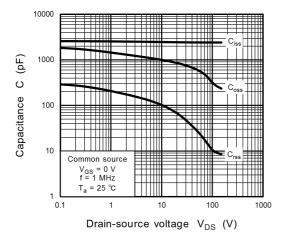


Fig. 8.11 Capacitance - V_{DS}

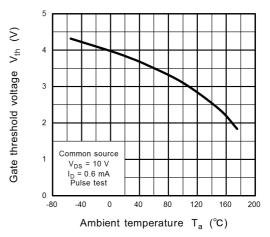


Fig. 8.8 V_{th} - T_a

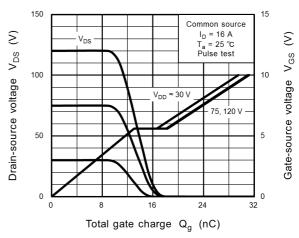


Fig. 8.10 Dynamic Input/Output Characteristics

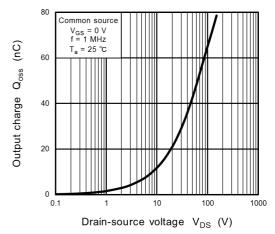


Fig. 8.12 Qoss - VDS



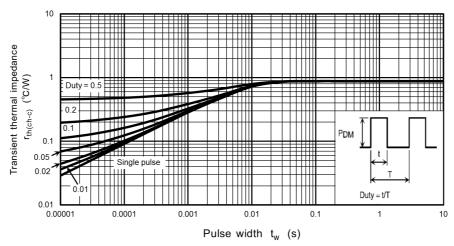


Fig. 8.13 r_{th} - t_w (Guaranteed Maximum)

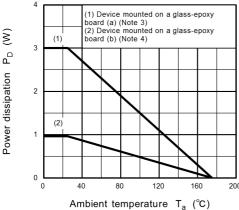


Fig. 8.14 P_D - T_a (Guaranteed Maximum)

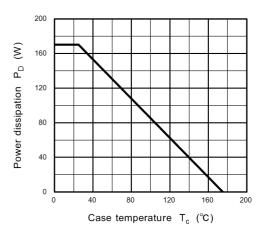


Fig. 8.15 P_D - T_c (Guaranteed Maximum)

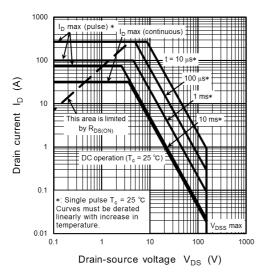


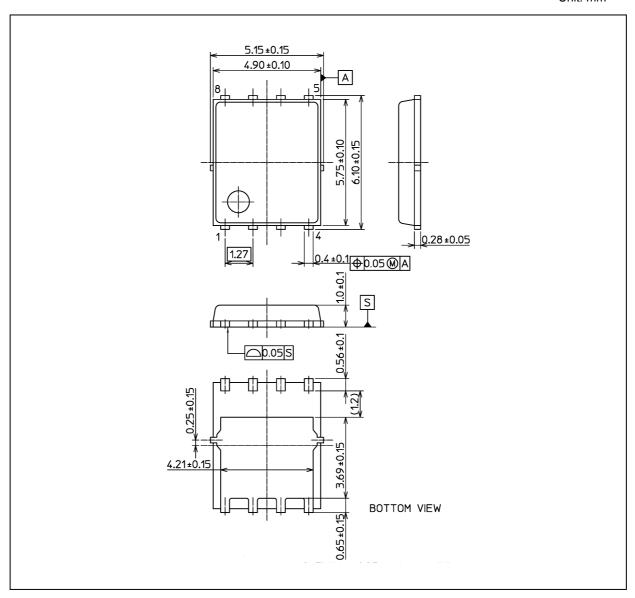
Fig. 8.16 Safe Operating Area (Guaranteed Maximum)

Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.



Package Dimensions

Unit: mm



Weight: 0.105 g (typ.)

| Package Name(s) |
|--------------------------|
| TOSHIBA: 2-5W1A |
| Nickname: SOP Advance(N) |



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